

IGBT Chip in NPT-technology

FEATURES:

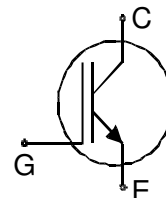
- 600V NPT technology
- 100µm chip
- short circuit prove
- positive temperature coefficient
- easy paralleling

This chip is used for:

- SGP20N60

Applications:

- drives



Chip Type	V _{CE}	I _{CN}	Die Size	Package	Ordering Code
SIGC18T60SNC	600V	20A	4.3 x 4.3 mm ²	sawn on foil	Q67041-S2856-A001
SIGC18T60SNC	600V	20A	4.3 x 4.3 mm ²	unsawn	Q67041-S2856-A002

MECHANICAL PARAMETER:

Raster size	4.3 x 4.3	mm ²
Area total / active	18.49 / 14.3	
Emitter pad size	2.48 x 2.98	
Gate pad size	0.7 x 1.08	
Thickness	100	µm
Wafer size	150	mm
Flat position	270	deg
Max.possible chips per wafer	796	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm Al Si 1%	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, ≤500µm	
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j=25^\circ\text{C}$	V_{CE}	600	V
DC collector current, limited by T_{jmax}	I_C	¹⁾	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	60	A
Gate emitter voltage	V_{GE}	± 20	V
Operating junction and storage temperature	T_j, T_{stg}	-55 ... +150	$^\circ\text{C}$

¹⁾ depending on thermal properties of assembly

STATIC CHARACTERISTICS (tested on chip), $T_j=25^\circ\text{C}$, unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}, I_C=500\mu\text{A}$	600			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15\text{V}, I_C=20\text{A}$	1.6	1.9	2.5	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=500\mu\text{A}, V_{GE}=V_{CE}$	3	4	5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600\text{V}, V_{GE}=0\text{V}$			1.5	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0\text{V}, V_{GE}=20\text{V}$			120	nA

DYNAMIC CHARACTERISTICS (tested at component):

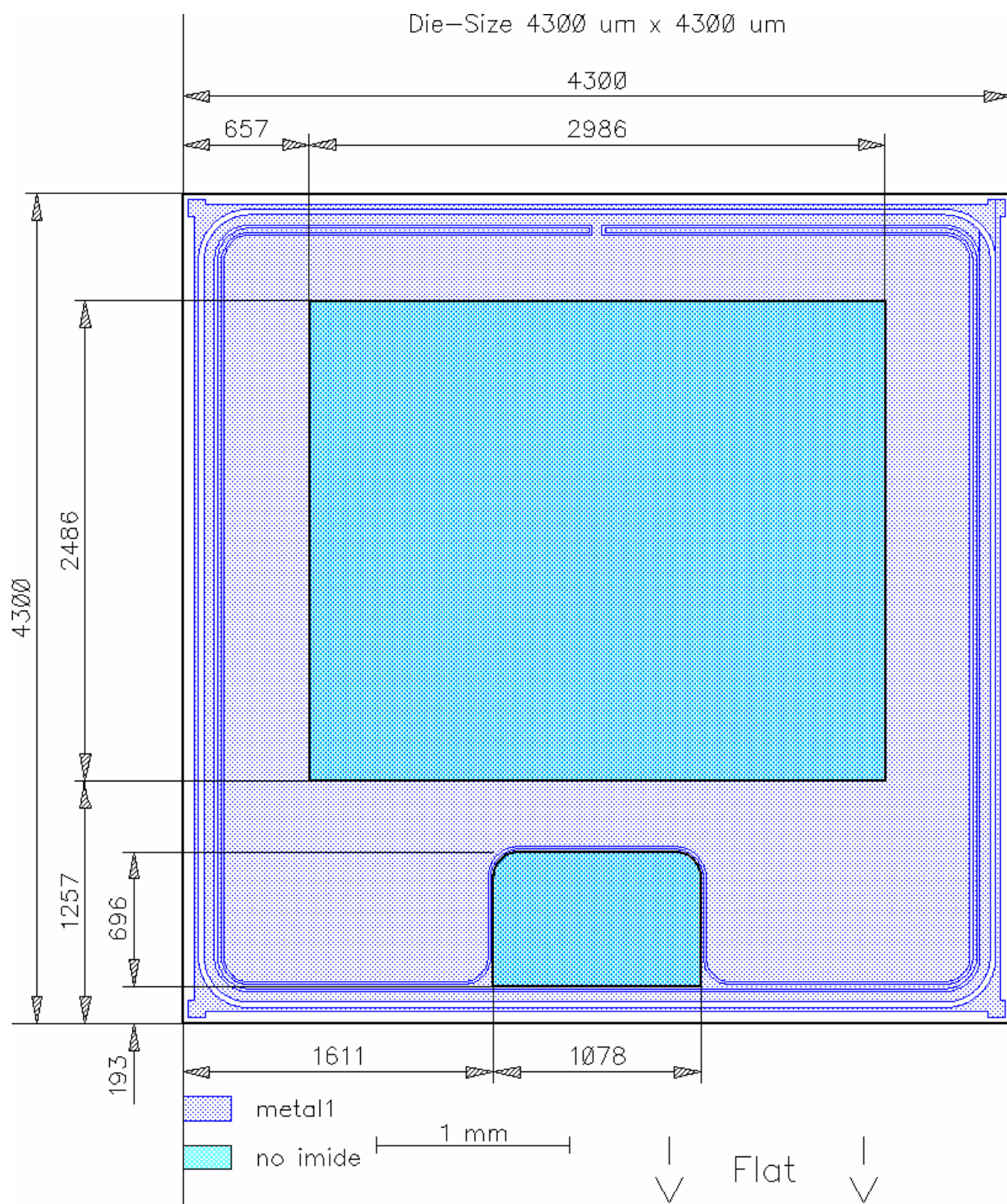
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	$V_{CE}=25\text{V}$	-	1100	1320	pF
Output capacitance	C_{oss}	$V_{GE}=0\text{V}$	-	107	128	
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$	-	63	75	

SWITCHING CHARACTERISTICS (tested at component), Inductive Load:

Parameter	Symbol	Conditions ²⁾	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$	-	36	46	ns
Rise time	t_r	$V_{CC}=400\text{V}$	-	30	36	
Turn-off delay time	$t_{d(off)}$	$I_C=20\text{A}$	-	250	300	
Fall time	t_f	$V_{GE}=+15/0\text{V}$ $R_G=16\Omega$	-	63	76	

²⁾ switching conditions different to 600V Standard IGBT 2, under comparable switching conditions 40% faster turnoff than Standard IGBT 2. Values also influenced by parasitic L- and C- in measurement and package.

CHIP DRAWING:





SIGC18T60SNC

FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet

SGP20N60

Package :TO220

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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